

PMDPB55XP 20 V, dual P-channel Trench MOSFET Rev. 3 – 4 June 2012

Product data sheet

1. **Product profile**

1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- 1.3 Applications
 - Charging switch for portable devices
 - DC/DC converters
 - Small brushless DC motor drive

- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Power management in battery-driven portables
- Hard disc and computing power management

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transi	stor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-	-4.5	А
Static cha	racteristics (per transistor)						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3.4 A; T_j = 25 °C		-	55	70	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		54 50
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2	7 8	
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	G1 S1 S2 G2
7	D1	drain TR1	Transparent top view	017aaa258
8	D2	drain TR2	SOT1118 (DFN2020-6)	

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMDPB55XP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118			

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMDPB55XP	1Z

5. Limiting values

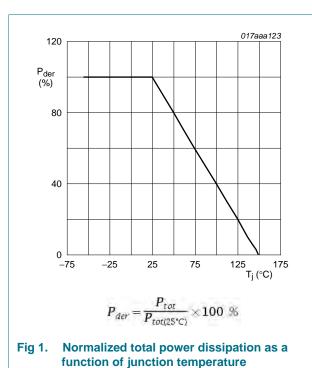
Table 5. Limiting values

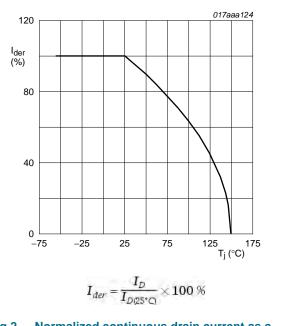
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Per transist	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-4.5	А
		V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-3.4	А
		V_{GS} = -4.5 V; T_{amb} = 100 °C	<u>[1]</u>	-	-2.2	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-14	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	1170	mW
		T _{sp} = 25 °C		-	8300	mW
Source-drai	in diode					
I _S	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1.2	А
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

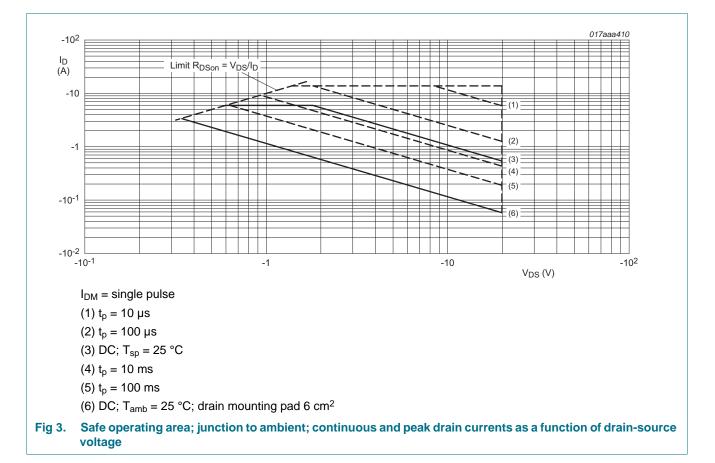






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6. Thermal characteristics

Table 6. Thermal cha	aracteristics
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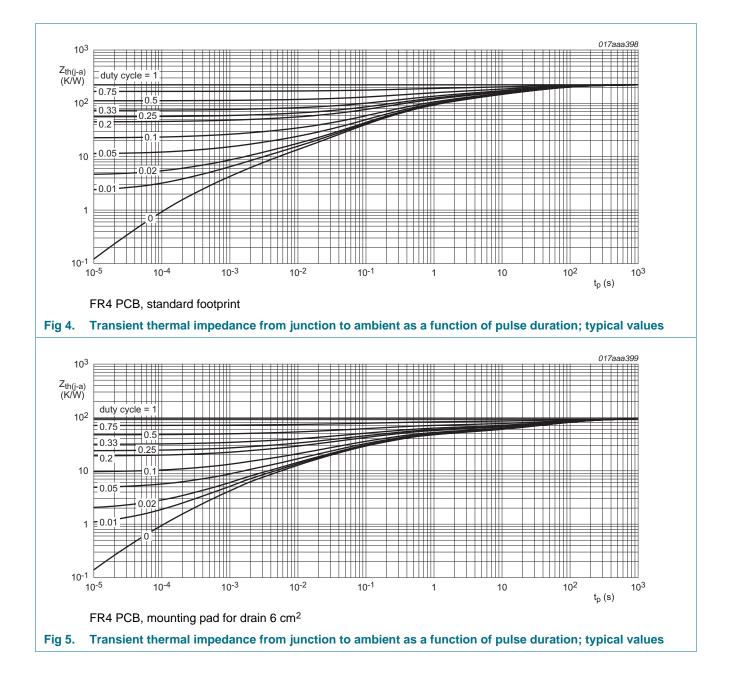
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	223	256	K/W
	from junction to ambient	[2]	[2]	-	93	107	K/W
		in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point	in free air		-	10	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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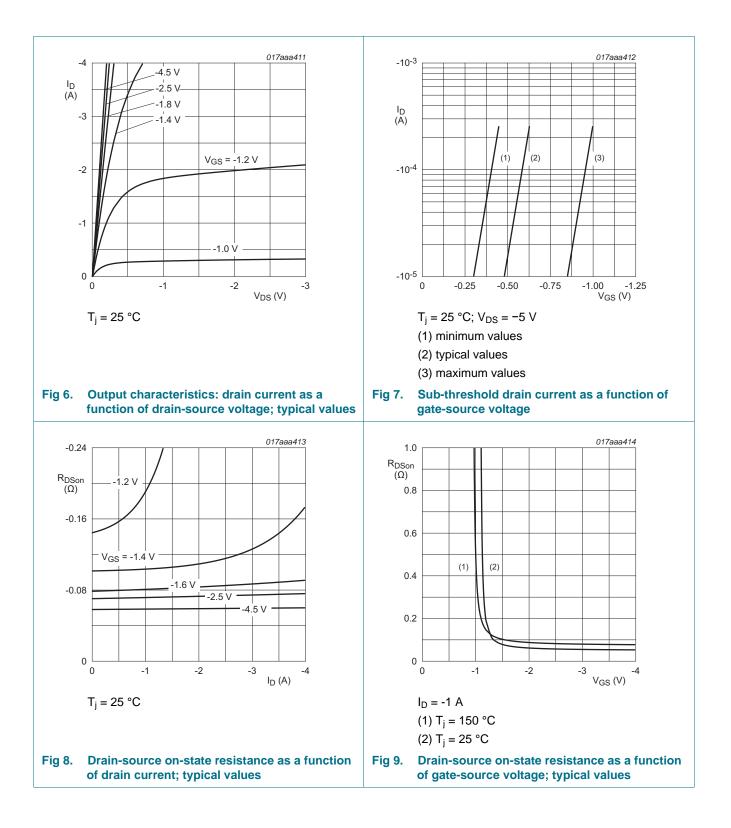
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}C$	-0.47	-0.65	-0.9	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R_{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -3.4 A; T _j = 25 °C	-	55	70	mΩ
	resistance	V_{GS} = -4.5 V; I _D = -3.4 A; T _j = 150 °C	-	78	99	mΩ
		V_{GS} = -2.5 V; I_D = -1.6 A; T_j = 25 °C	-	75	90	mΩ
		V_{GS} = -1.8 V; I _D = -1.5 A; T _j = 25 °C	-	110	135	mΩ
g _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -3.4 A; T_j = 25 °C	-	15	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.4 A; V_{GS} = -5 V;	-	16.5	25	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	1.65	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	785	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	80	-	pF
C _{rss}	reverse transfer capacitance		-	64	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3.4 A; V_{GS} = -5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 $ °C	-	14	-	ns
t _{d(off)}	turn-off delay time		-	135	-	ns
t _f	fall time		-	68	-	ns
Source-d	rain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = -1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.8	-1.2	V

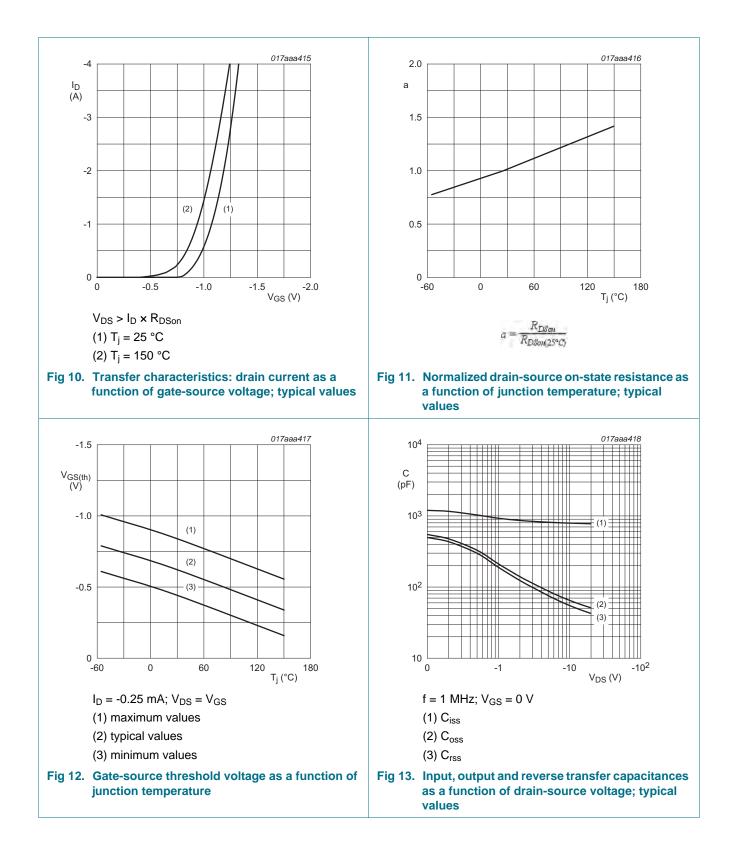
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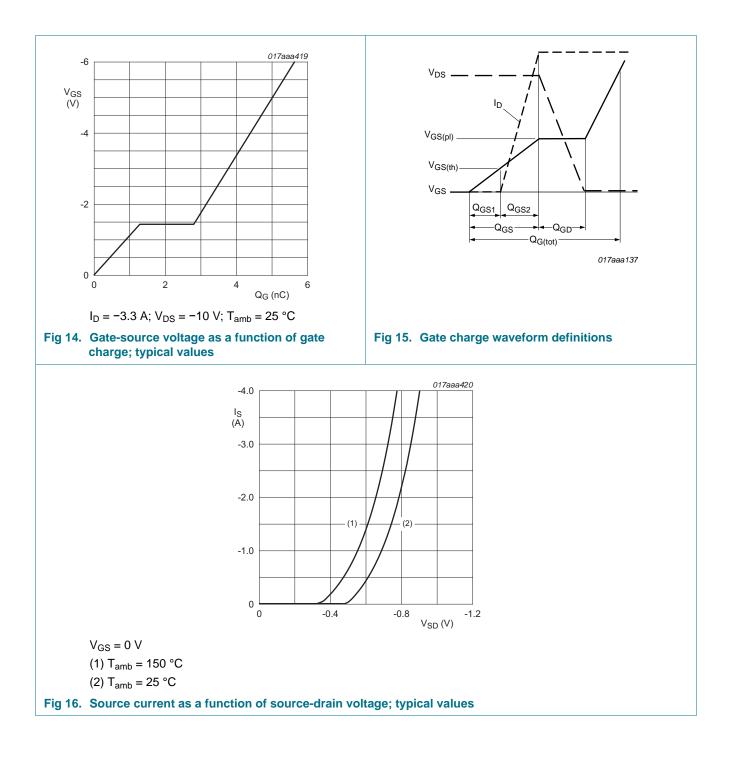
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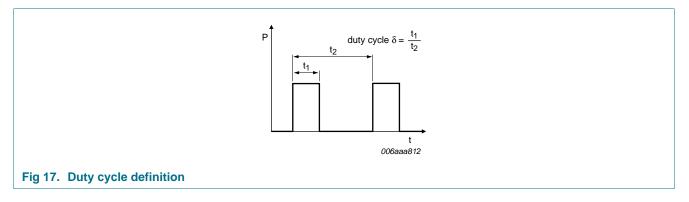
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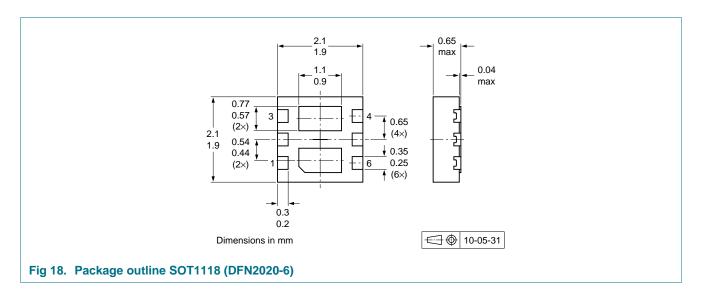


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8. Test information

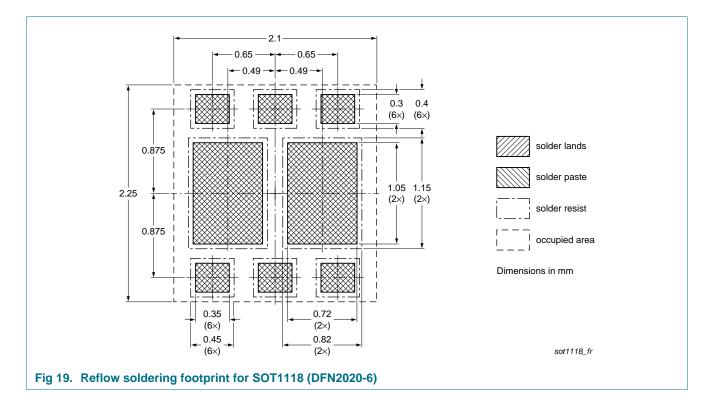


9. Package outline



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10. Soldering



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11. Revision history

Table 8.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB55XP v.3	20120604	Product data sheet	-	PMDPB55XP v.2
Modifications:	 <u>Table 7.</u>: V_{GSt} 	h values updated		
PMDPB55XP v.2	20120502	Product data sheet	-	PMDPB55XP v.1
PMDPB55XP v.1	20120309	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

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